Final datasheet
EasyPACK™ module with CoolSiC™ Trench MOSFET and PressFIT / NTC

Features

Typical appearance

- Electrical features
  - V_{DSS} = 1200 V
  - I_{DN} = 50 A / I_{DRM} = 100 A
  - Low inductive design
  - High current density
  - Suitable Infineon gate drivers can be found under https://www.infineon.com/gdfinder
- Mechanical features
  - PressFIT contact technology
  - Integrated NTC temperature sensor
  - Rugged mounting due to integrated mounting clamps

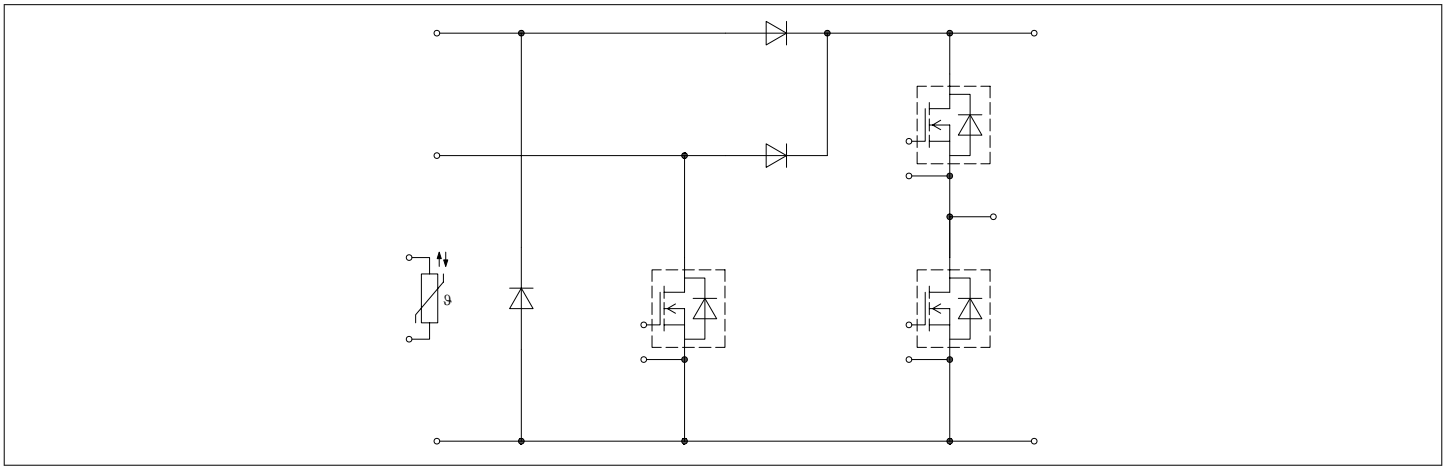
Potential applications

- Solar applications

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description



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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f = 50 Hz, *t* = 1 min	3.0	kV
Isolation test voltage NTC	$V_{ISOL(NTC)}$	RMS, f = 50 Hz, *t* = 1 min	3.0	kV
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Comparative tracking index	*CTI*		> 200	
Relative thermal index (electrical)	*RTI*	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			14		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	T_H = 25 °C, per switch		3.5		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	T_H = 25 °C, per switch		2.7		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting force per clamp	*F*		20		50	N
Weight	*G*			24		g

***Note**: The current under continuous operation is limited to 25 A rms per connector pin.*

2 MOSFET

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}		T_{vj} = 25 °C	1200	V
Continuous DC drain current	I_{DDC}	T_{vj} = 175 °C, V_{GS} = 18 V	T_H = 80 °C	50	A
Repetitive peak drain current	I_{DRM}	verified by design, t_p limited by T_{vjmax}		100	A
Gate-source voltage, max. transient voltage	V_{GS}	*D* < 0.01		-10/23	V
Gate-source voltage, max. static voltage	V_{GS}			-7/20	V

Table 4 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		15...18	V
Off-state gate voltage	$V_{GS(off)}$		-5...0	V

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-resistance	$R_{DS(on)}$	I_D = 50 A	V_{GS} = 18 V, T_{vj} = 25 °C		16.2	24	mΩ
			V_{GS} = 18 V, T_{vj} = 125 °C		26.1		
			V_{GS} = 18 V, T_{vj} = 175 °C		34.7		
			V_{GS} = 15 V, T_{vj} = 25 °C		19.4		
Gate threshold voltage	$V_{GS(th)}$	I_D = 20 mA, V_{DS} = V_{GS}, T_{vj} = 25 °C, (tested after 1ms pulse at V_{GS} = +20 V)		3.45	4.3	5.15	V
Total gate charge	Q_G	V_{DD} = 800 V, V_{GS} = -3/18 V, T_{vj} = 25 °C			0.149		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			4.1		Ω
Input capacitance	C_{ISS}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		4.4		nF
Output capacitance	C_{OSS}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.21		nF
Reverse transfer capacitance	C_{rss}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.014		nF
C_{OSS} stored energy	E_{OSS}	V_{DS} = 800 V, V_{GS} = -3/18 V, T_{vj} = 25 °C			86		µJ
Drain-source leakage current	I_{DSS}	V_{DS} = 1200 V, V_{GS} = -3 V	T_{vj} = 25 °C		0.03	210	µA
Gate-source leakage current	I_{GSS}	V_{DS} = 0 V, T_{vj} = 25 °C	V_{GS} = 20 V			400	nA
Turn-on delay time (inductive load)	$t_{d\,on}$	I_D = 50 A, R_{Gon} = 1.1 Ω, V_{DD} = 600 V, V_{GS} = -3/18 V, t_{dead} = 1000 ns, 0.1 V_{GS} to 0.1 I_D	T_{vj} = 25 °C		27		ns
			T_{vj} = 125 °C		27		
			T_{vj} = 175 °C		27		
Rise time (inductive load)	t_r	I_D = 50 A, R_{Gon} = 1.1 Ω, V_{DD} = 600 V, V_{GS} = -3/18 V, t_{dead} = 1000 ns, 0.1 I_D to 0.9 I_D	T_{vj} = 25 °C		18		ns
			T_{vj} = 125 °C		18		
			T_{vj} = 175 °C		18		

(table continues...)

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-off delay time (inductive load)	$t_{d\,off}$	I_D = 50 A, R_{Goff} = 1 Ω, V_{DD} = 600 V, V_{GS} = -3/18 V, 0.9 V_{GS} to 0.9 I_D	T_{vj} = 25 °C		52		ns
			T_{vj} = 125 °C		56		
			T_{vj} = 175 °C		58		
Fall time (inductive load)	t_f	I_D = 50 A, R_{Goff} = 1 Ω, V_{DD} = 600 V, V_{GS} = -3/18 V, 0.9 I_D to 0.1 I_D	T_{vj} = 25 °C		9		ns
			T_{vj} = 125 °C		8		
			T_{vj} = 175 °C		8		
Turn-on energy loss per pulse	E_{on}	I_D = 50 A, V_{DD} = 600 V, L_σ = 15 nH, V_{GS} = -3/18 V, R_{Gon} = 1.1 Ω, di/dt = 7.36 kA/µs (T_{vj} = 175 °C), t_{dead} = 1000 ns	T_{vj} = 25 °C		0.38		mJ
			T_{vj} = 125 °C		0.38		
			T_{vj} = 175 °C		0.38		
Turn-off energy loss per pulse	E_{off}	I_D = 50 A, V_{DD} = 600 V, L_σ = 15 nH, V_{GS} = -3/18 V, R_{Goff} = 1 Ω, dv/dt = 57.8 kV/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		0.11		mJ
			T_{vj} = 125 °C		0.12		
			T_{vj} = 175 °C		0.12		
Thermal resistance, junction to heat sink	R_{thJH}	per MOSFET, λ_{grease} = 1 W/(m·K)			0.825		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C

***Note**: The selection of positive and negative gate-source voltages impacts losses and the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2021-13 must be considered to ensure sound operation of the device over the planned lifetime.*
Tvj,op > 150°C is allowed for operation at overload conditions for MOSFET and body diode. For detailed specifications, please refer to AN 2021-13

3 Body diode (MOSFET)

Table 6 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
DC body diode forward current	I_{SD}	T_{vj} = 175 °C, V_{GS} = -3 V	T_H = 80 °C	25	A

Table 7 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_{SD}	I_{SD} = 50 A, V_{GS} = -3 V	T_{vj} = 25 °C		4.2	5.35	V
			T_{vj} = 125 °C		3.9		
			T_{vj} = 175 °C		3.8		

4 MOSFET, T2 / T3

Table 8 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}		T_{vj} = 25 °C	1200	V
Continuous DC drain current	I_{DDC}	T_{vj} = 175 °C, V_{GS} = 18 V	T_H = 90 °C	25	A
Repetitive peak drain current	I_{DRM}	verified by design, t_p limited by T_{vjmax}		50	A
Gate-source voltage, max. transient voltage	V_{GS}	D < 0.01		-10/23	V
Gate-source voltage, max. static voltage	V_{GS}			-7/20	V

Table 9 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		15...18	V
Off-state gate voltage	$V_{GS(off)}$		-5...0	V

Table 10 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-resistance	$R_{DS(on)}$	I_D = 25 A	V_{GS} = 18 V, T_{vj} = 25 °C		32.3	48	mΩ
			V_{GS} = 18 V, T_{vj} = 125 °C		52.2		
			V_{GS} = 18 V, T_{vj} = 175 °C		69.4		
			V_{GS} = 15 V, T_{vj} = 25 °C		38.8		
Gate threshold voltage	$V_{GS(th)}$	I_D = 10 mA, V_{DS} = V_{GS}, T_{vj} = 25 °C, (tested after 1ms pulse at V_{GS} = +20 V)		3.45	4.3	5.15	V
Total gate charge	Q_G	V_{DD} = 800 V, V_{GS} = -3/18 V, T_{vj} = 25 °C			0.074		µC

(table continues...)

Table 10 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			8.2		Ω
Input capacitance	C_{ISS}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		2.2		nF
Output capacitance	C_{OSS}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.105		nF
Reverse transfer capacitance	C_{rss}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.007		nF
C_{OSS} stored energy	E_{OSS}	V_{DS} = 800 V, V_{GS} = -3/18 V, T_{vj} = 25 °C			43		µJ
Drain-source leakage current	I_{DSS}	V_{DS} = 1200 V, V_{GS} = -3 V	T_{vj} = 25 °C		0.015	110	µA
Gate-source leakage current	I_{GSS}	V_{DS} = 0 V, T_{vj} = 25 °C	V_{GS} = 20 V			400	nA
Turn-on delay time (inductive load)	$t_{d\,on}$	I_D = 25 A, R_{Gon} = 4.7 Ω, V_{DD} = 600 V, V_{GS} = -3/18 V, t_{dead} = 1000 ns, 0.1 V_{GS} to 0.1 I_D	T_{vj} = 25 °C		29		ns
			T_{vj} = 125 °C		30		
			T_{vj} = 175 °C		30		
Rise time (inductive load)	t_r	I_D = 25 A, R_{Gon} = 4.7 Ω, V_{DD} = 600 V, V_{GS} = -3/18 V, t_{dead} = 1000 ns, 0.1 I_D to 0.9 I_D	T_{vj} = 25 °C		21		ns
			T_{vj} = 125 °C		22		
			T_{vj} = 175 °C		23		
Turn-off delay time (inductive load)	$t_{d\,off}$	I_D = 25 A, R_{Goff} = 0.24 Ω, V_{DD} = 600 V, V_{GS} = -3/18 V, 0.9 V_{GS} to 0.9 I_D	T_{vj} = 25 °C		46		ns
			T_{vj} = 125 °C		49		
			T_{vj} = 175 °C		51		
Fall time (inductive load)	t_f	I_D = 25 A, R_{Goff} = 0.24 Ω, V_{DD} = 600 V, V_{GS} = -3/18 V, 0.9 I_D to 0.1 I_D	T_{vj} = 25 °C		11		ns
			T_{vj} = 125 °C		10		
			T_{vj} = 175 °C		10		
Turn-on energy loss per pulse	E_{on}	I_D = 25 A, V_{DD} = 600 V, L_σ = 15 nH, V_{GS} = -3/18 V, R_{Gon} = 4.7 Ω, di/dt = 4.65 kA/µs (T_{vj} = 175 °C), t_{dead} = 1000 ns	T_{vj} = 25 °C		0.3		mJ
			T_{vj} = 125 °C		0.39		
			T_{vj} = 175 °C		0.46		
Turn-on energy loss per pulse, optimized	$E_{on,o}$	I_D = 25 A, V_{DD} = 600 V, L_σ = 15 nH, V_{GS} = -3/18 V, $R_{Gon,o}$ = 4.3 Ω, di/dt = 4.51 kA/µs (T_{vj} = 175 °C), t_{dead} = 100 ns	T_{vj} = 25 °C		0.29		mJ
			T_{vj} = 125 °C		0.34		
			T_{vj} = 175 °C		0.39		

(table continues...)

Table 10 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-off energy loss per pulse	E_{off}	I_D = 25 A, V_{DD} = 600 V, L_σ = 15 nH, V_{GS} = -3/18 V, R_{Goff} = 0.24 Ω, dv/dt = 46.8 kV/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		0.049		mJ
			T_{vj} = 125 °C		0.049		
			T_{vj} = 175 °C		0.049		
Thermal resistance, junction to heat sink	R_{thJH}	per MOSFET, λ_{grease} = 1 W/(m·K)			1.42		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C

***Note**: The selection of positive and negative gate-source voltages impacts losses and the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2021-13 must be considered to ensure sound operation of the device over the planned lifetime.*

$T_{vj,op}$ > 150°C is allowed for operation at overload conditions for MOSFET and body diode. For detailed specifications, please refer to AN 2021-13.

5 Body diode (MOSFET, T2 / T3)

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
DC body diode forward current	I_{SD}	T_{vj} = 175 °C, V_{GS} = -3 V	T_H = 90 °C	14	A

Table 12 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_{SD}	I_{SD} = 25 A, V_{GS} = -3 V	T_{vj} = 25 °C		4.2	5.35	V
			T_{vj} = 125 °C		3.9		
			T_{vj} = 175 °C		3.8		
Peak reverse recovery current	I_{rrm}	I_{SD} = 25 A, di_s/dt = 4.65 kA/µs, V_{DD} = 600 V, V_{GS}=-3 V, t_{dead} = 1000 ns	T_{vj} = 25 °C		36		A
			T_{vj} = 125 °C		44		
			T_{vj} = 175 °C		51		
Recovered charge	Q_{rr}	I_{SD} = 25 A, di_s/dt = 4.65 kA/µs, V_{DD} = 600 V, V_{GS}=-3 V, t_{dead} = 1000 ns	T_{vj} = 25 °C		0.66		µC
			T_{vj} = 125 °C		0.86		
			T_{vj} = 175 °C		1		
Reverse recovery energy	E_{rec}	I_{SD} = 25 A, di_s/dt = 4.65 kA/µs (T_{vj} = 175 °C), V_{DD} = 600 V, V_{GS}=-3 V, t_{dead} = 1000 ns	T_{vj} = 25 °C		0.027		mJ
			T_{vj} = 125 °C		0.094		
			T_{vj} = 175 °C		0.14		

(table continues...)

Table 12 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Reverse recovery energy, optimized	$E_{rec,o}$	I_{SD} = 25 A, di_s/dt = 4.51 kA/µs (T_{vj} = 175 °C), V_{DD} = 600 V, V_{GS} = -3 V, t_{dead} = 100 ns	T_{vj} = 25 °C		0.023		mJ
			T_{vj} = 125 °C		0.058		
			T_{vj} = 175 °C		0.09		

6 Diode, Boost

Table 13 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	1200	V
Continuous DC forward current	I_F			40	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		80	A
I^2t - value	I^2t	t_P = 10 ms, V_R = 0 V	T_{vj} = 125 °C	320	A^2s
			T_{vj} = 150 °C	295	

Table 14 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 40 A, V_{GE} = 0 V	T_{vj} = 25 °C		1.40	1.85	V
			T_{vj} = 125 °C		1.70		
			T_{vj} = 150 °C		1.85		
Thermal resistance, junction to heat sink	R_{thJH}	per diode, λ_{grease} = 1 W/(m·K)			0.836		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150	°C

7 Bypass-diode

Table 15 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	1200	V
Maximum RMS forward current per chip	I_{FRMSM}	T_H = 100 °C		50	A

(table continues...)

Table 15 (continued) Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Maximum RMS current at rectifier output	I_{RMSM}	T_H = 100 °C		50	A
Surge forward current	I_{FSM}	t_p = 10 ms	T_{vj} = 25 °C	450	A
			T_{vj} = 150 °C	360	
I²t - value	I^2t	t_p = 10 ms	T_{vj} = 25 °C	1010	A²s
			T_{vj} = 150 °C	648	

Table 16 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 30 A	T_{vj} = 150 °C		0.95		V
Reverse current	I_r	T_{vj} = 150 °C, V_R = 1200 V			0.1		mA
Thermal resistance, junction to heat sink	R_{thJH}	per diode, λ_{grease} = 1 W/(m·K)			0.859		K/W
Temperature under switching conditions	$T_{vj, op}$			-40		150	°C

8 Inverse-polarity protection diode

Table 17 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	1200	V
Maximum RMS forward current per chip	I_{FRMSM}	T_H = 100 °C		50	A
Maximum RMS current at rectifier output	I_{RMSM}	T_H = 100 °C		50	A
Surge forward current	I_{FSM}	t_p = 10 ms	T_{vj} = 25 °C	450	A
			T_{vj} = 150 °C	360	
I²t - value	I^2t	t_p = 10 ms	T_{vj} = 25 °C	1010	A²s
			T_{vj} = 150 °C	648	

Table 18 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 30 A	T_{vj} = 150 °C		0.95		V
Reverse current	I_r	T_{vj} = 150 °C, V_R = 1200 V			0.1		mA

(table continues...)

Table 18 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to heat sink	R_{thJH}	per diode, λ_{grease} = 1 W/(m·K)		0.928		K/W
Temperature under switching conditions	$T_{vj, op}$		-40		150	°C

9 NTC-Thermistor

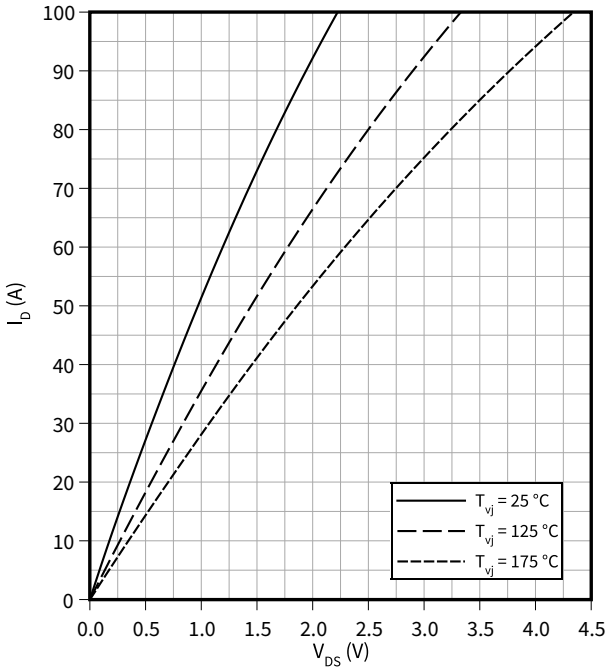
Table 19 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	T_{NTC} = 25 °C		5		kΩ
Deviation of R_{100}	$\Delta R/R$	T_{NTC} = 100 °C, R_{100} = 493 Ω	-5		5	%
Power dissipation	P_{25}	T_{NTC} = 25 °C			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2-1/(298{,}15\ K))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2-1/(298{,}15\ K))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2-1/(298{,}15\ K))]$		3433		K

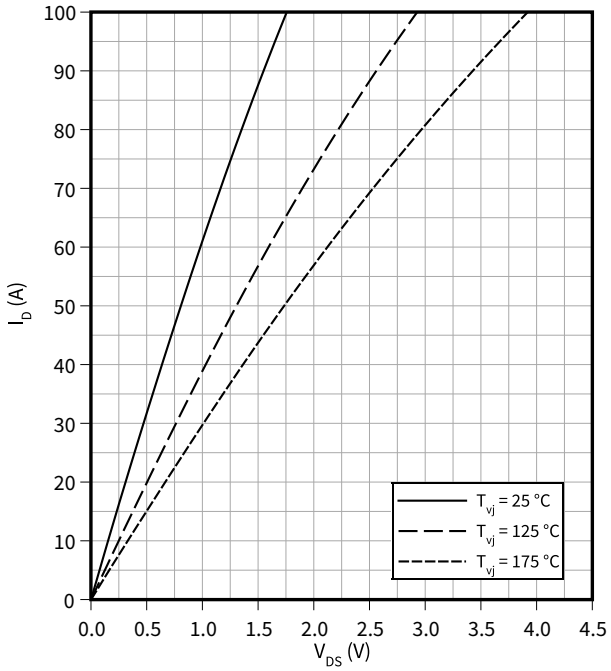
***Note**: For an analytical description of the NTC characteristics please refer to AN2009-10, chapter 4.*

10 Characteristics diagrams

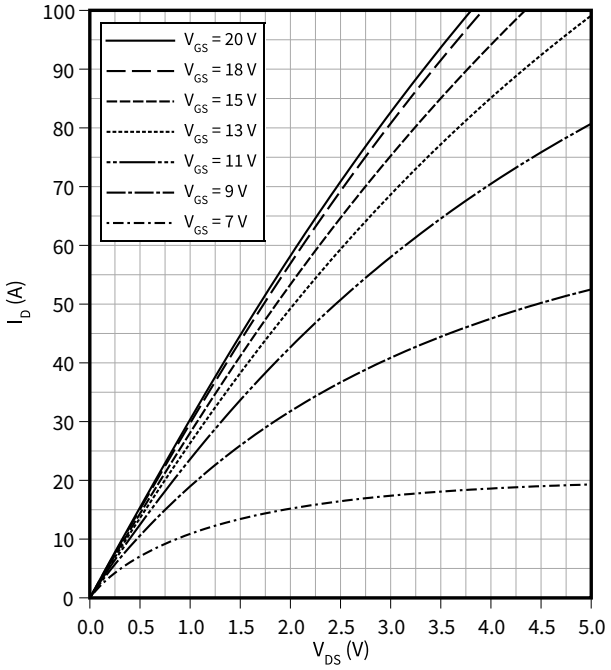
Output characteristic (typical), MOSFET
$I_D = f(V_{DS})$
V_{GS} = 15 V



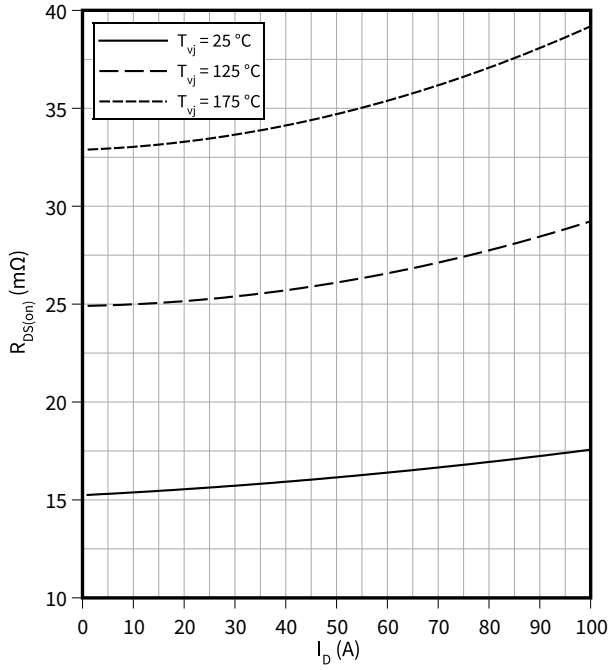
Output characteristic (typical), MOSFET
$I_D = f(V_{DS})$
V_{GS} = 18 V



Output characteristic field (typical), MOSFET
$I_D = f(V_{DS})$
T_{vj} = 175 °C

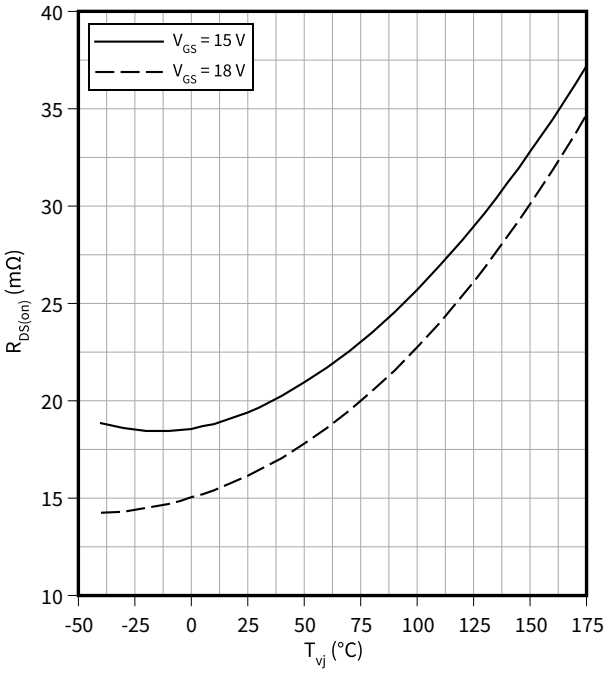


Drain source on-resistance (typical), MOSFET
$R_{DS(on)} = f(I_D)$
V_{GS} = 18 V



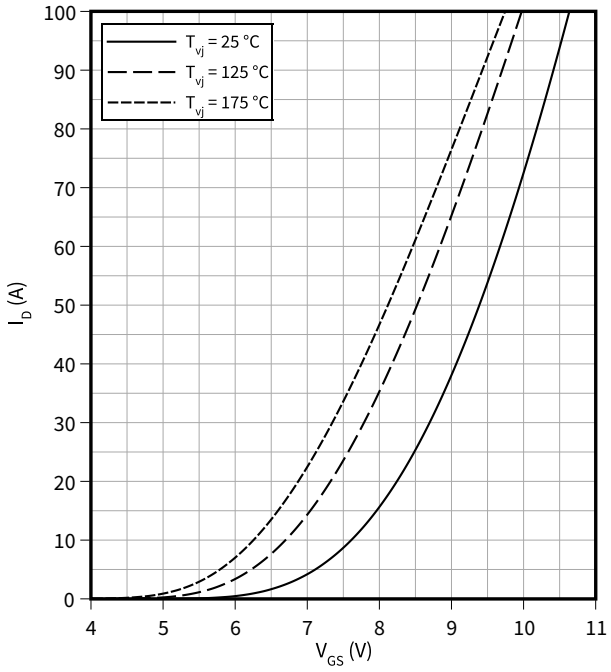
Drain source on-resistance (typical), MOSFET

$R_{DS(on)} = f(T_{vj})$
$I_D = 50$ A



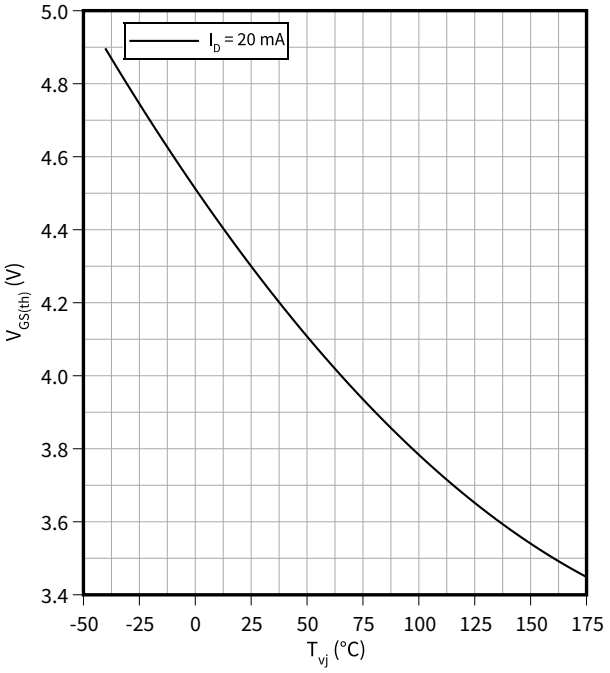
Transfer characteristic (typical), MOSFET

$I_D = f(V_{GS})$
$V_{DS} = 20$ V



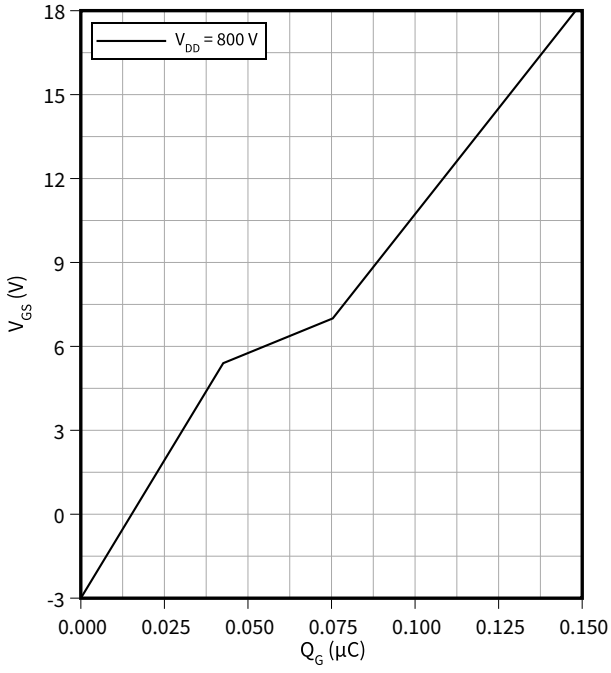
Gate-source threshold voltage (typical), MOSFET

$V_{GS(th)} = f(T_{vj})$
$V_{GS} = V_{DS}$



Gate charge characteristic (typical), MOSFET

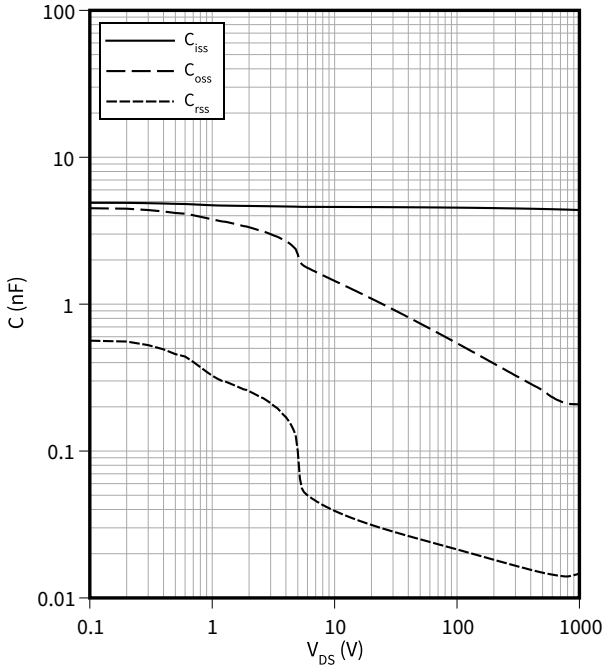
$V_{GS} = f(Q_G)$
$I_D = 50$ A, $T_{vj} = 25$ °C



Capacity characteristic (typical), MOSFET

C = f(V_{DS})

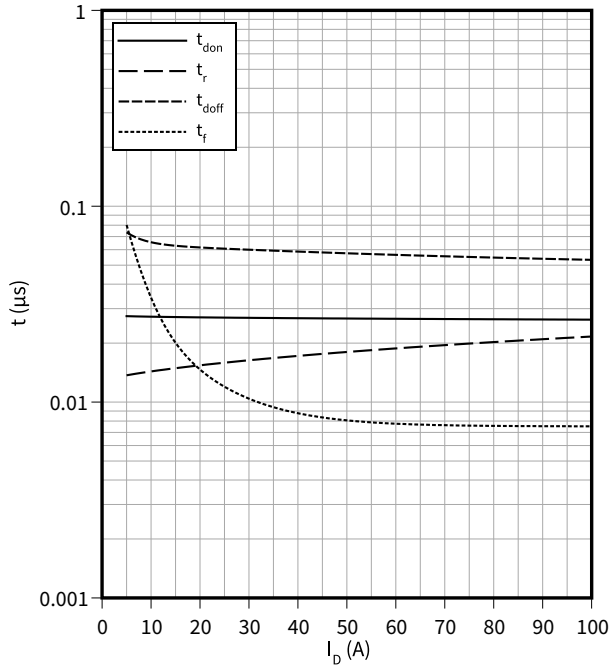
f = 100 kHz, T_{vj} = 25 °C, V_{GS} = 0 V



Switching times (typical), MOSFET

t = f(I_D)

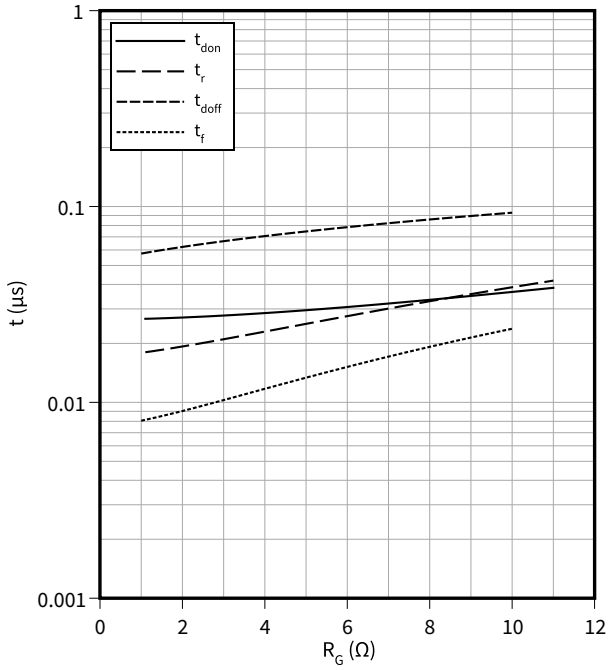
R_{Goff} = 1 Ω, R_{Gon} = 1.1 Ω, V_{DD} = 600 V, T_{vj} = 175 °C, V_{GS} = -3/18 V



Switching times (typical), MOSFET

t = f(R_G)

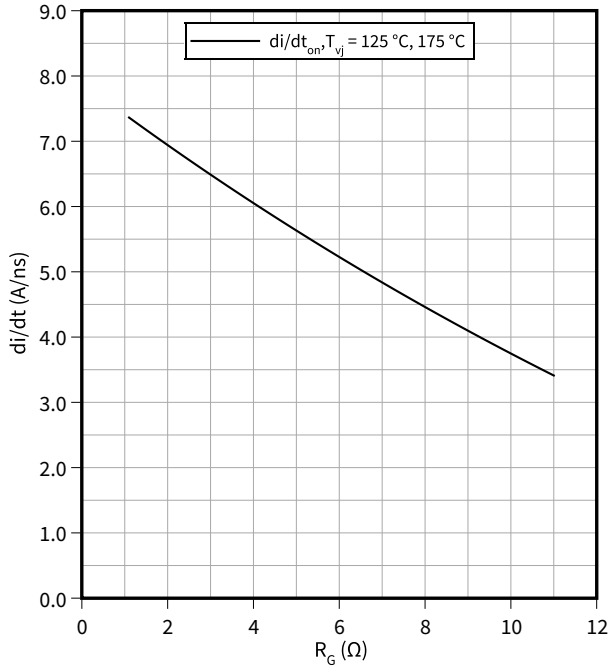
V_{DD} = 600 V, I_D = 50 A, T_{vj} = 175 °C, V_{GS} = -3/18 V



Current slope (typical), MOSFET

di/dt = f(R_G)

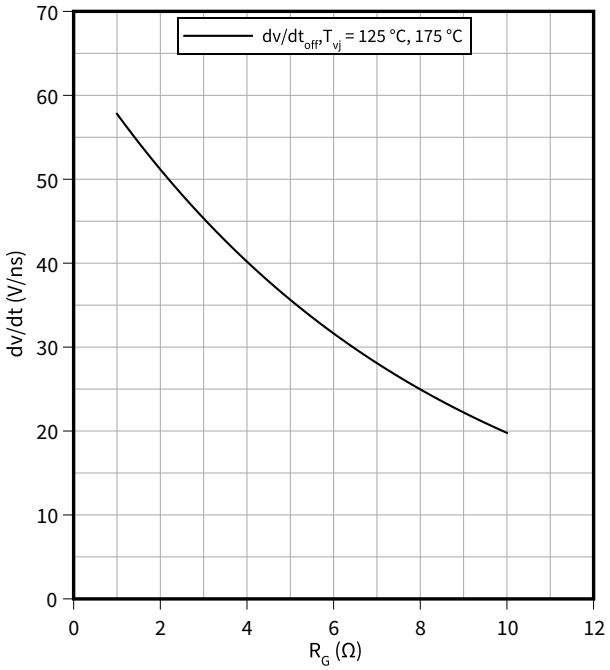
V_{DD} = 600 V, I_D = 50 A, V_{GS} = -3/18 V



Voltage slope (typical), MOSFET

$dv/dt = f(R_G)$

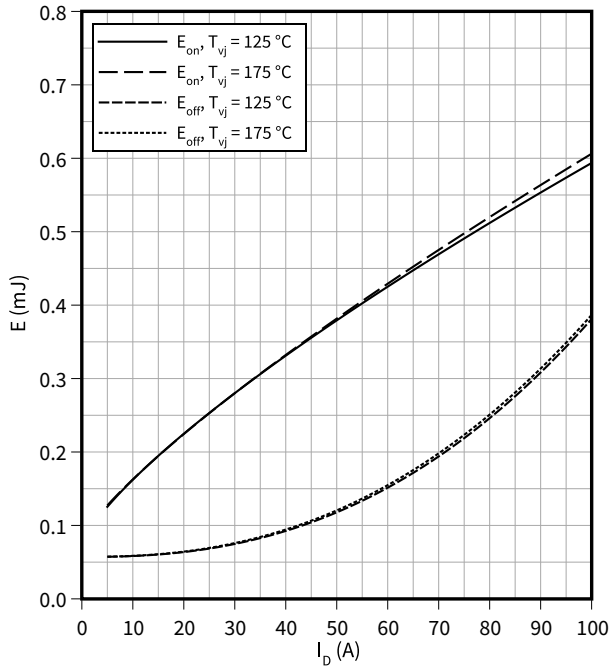
V_{DD} = 600 V, I_D = 50 A, V_{GS} = -3/18 V



Switching losses (typical), MOSFET

$E = f(I_D)$

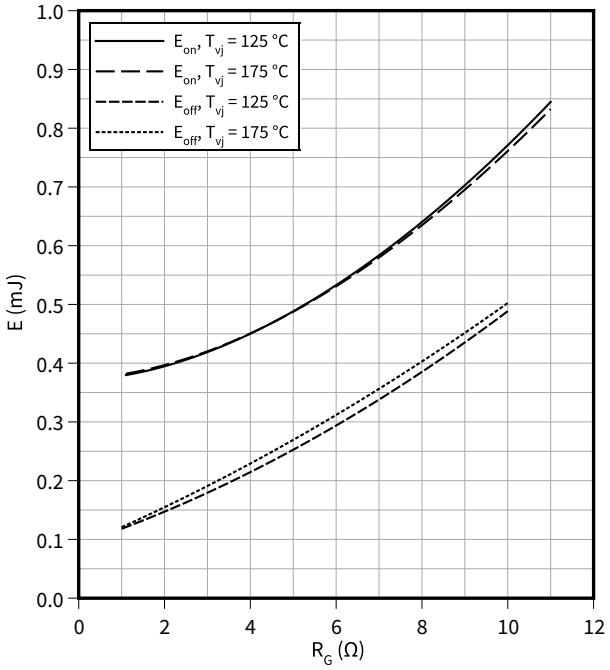
R_{Goff} = 1 Ω, R_{Gon} = 1.1 Ω, V_{DD} = 600 V, V_{GS} = -3/18 V



Switching losses (typical), MOSFET

$E = f(R_G)$

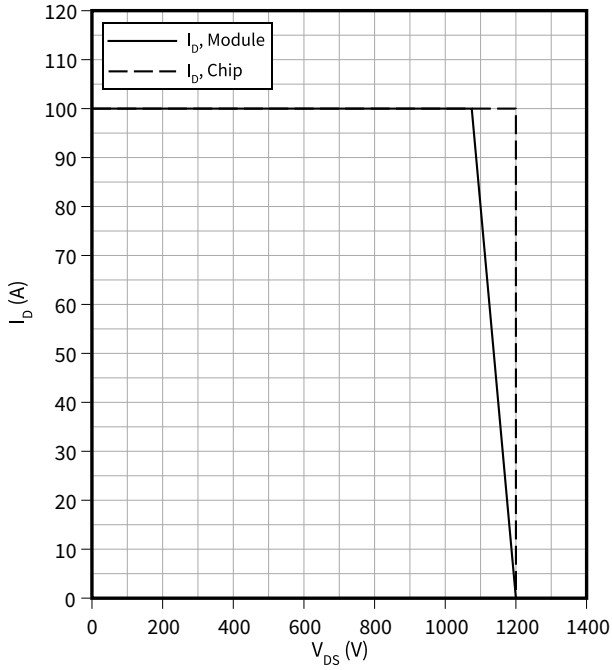
V_{DD} = 600 V, I_D = 50 A, V_{GS} = -3/18 V



Reverse bias safe operating area (RBSOA), MOSFET

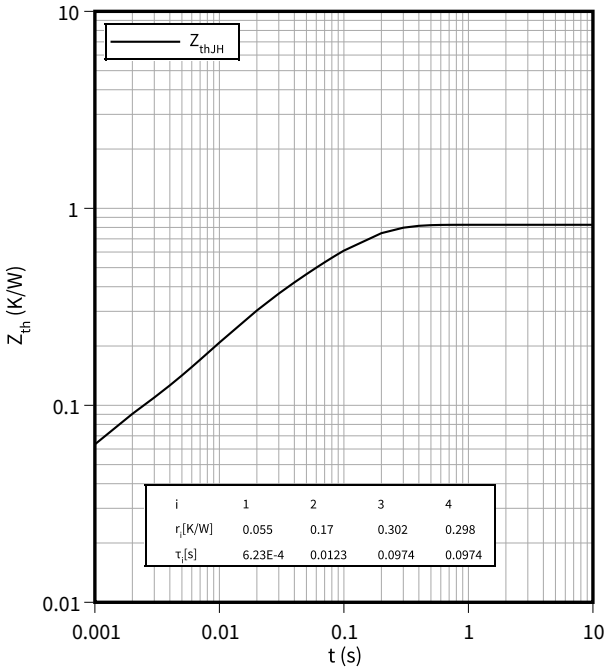
$I_D = f(V_{DS})$

R_{Goff} = 1 Ω, T_{vj} = 175 °C, V_{GS} = -3/18 V



Transient thermal impedance, MOSFET

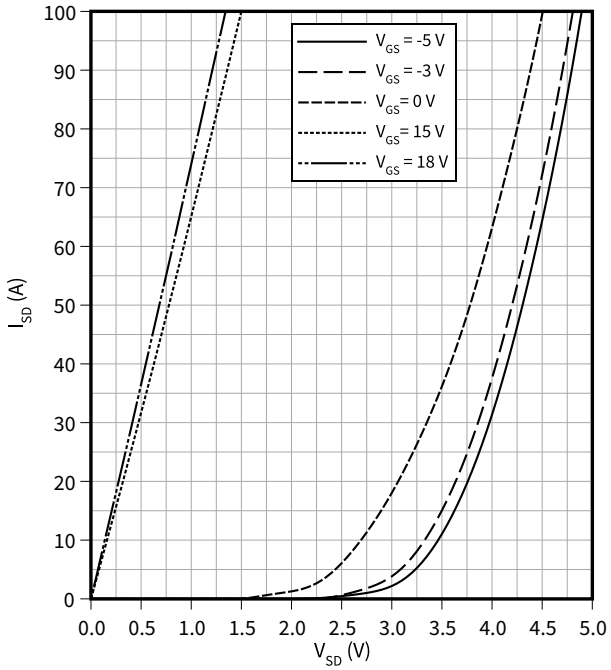
$Z_{th} = f(t)$



Forward characteristic body diode (typical), MOSFET

$I_{SD} = f(V_{SD})$

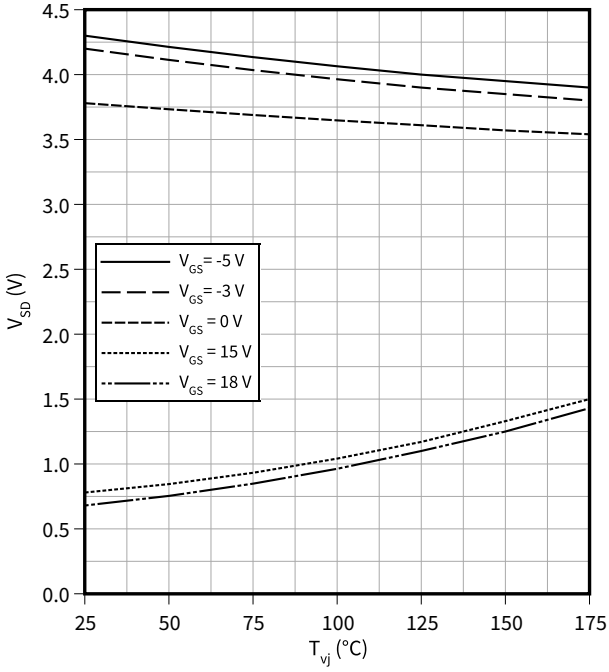
$T_{vj} = 25\ °C$



Forward characteristic body diode (typical), MOSFET

$V_{SD} = f(T_{vj})$

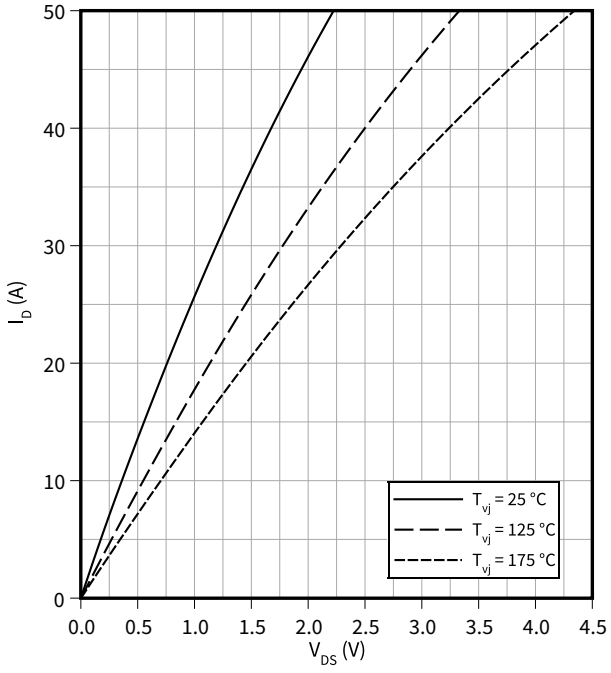
$I_{SD} = 50\ A$



Output characteristic (typical), MOSFET, T2 / T3

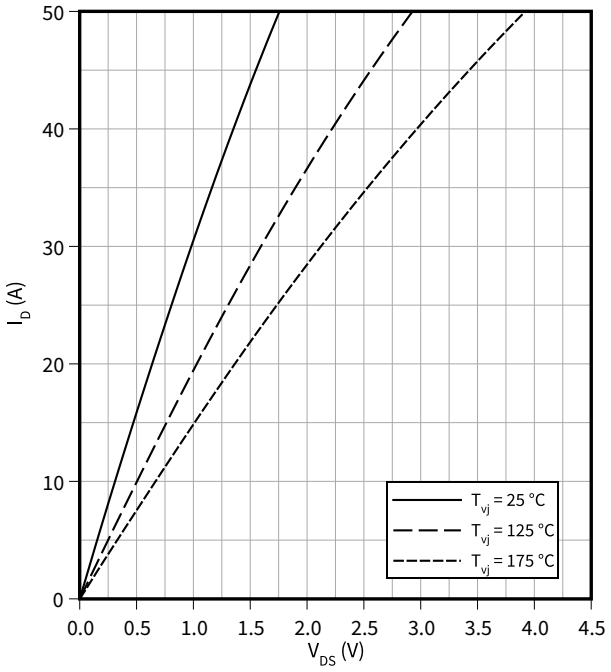
$I_D = f(V_{DS})$

$V_{GS} = 15\ V$



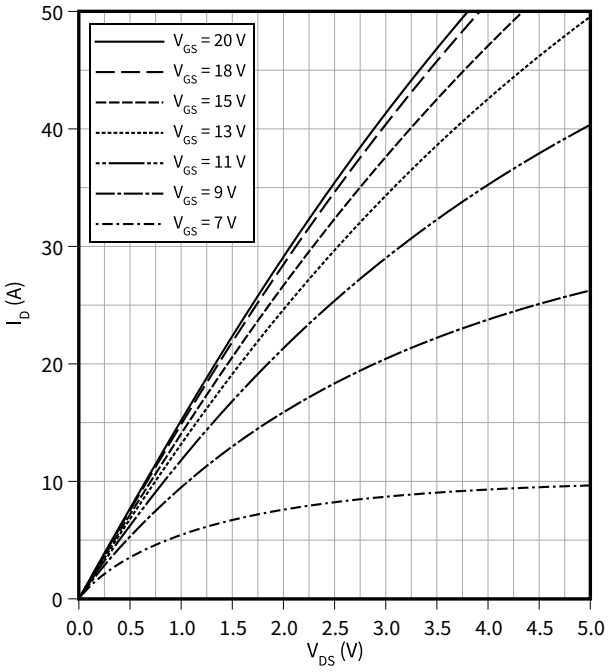
Output characteristic (typical), MOSFET, T2 / T3

$I_D = f(V_{DS})$
$V_{GS} = 18\ V$



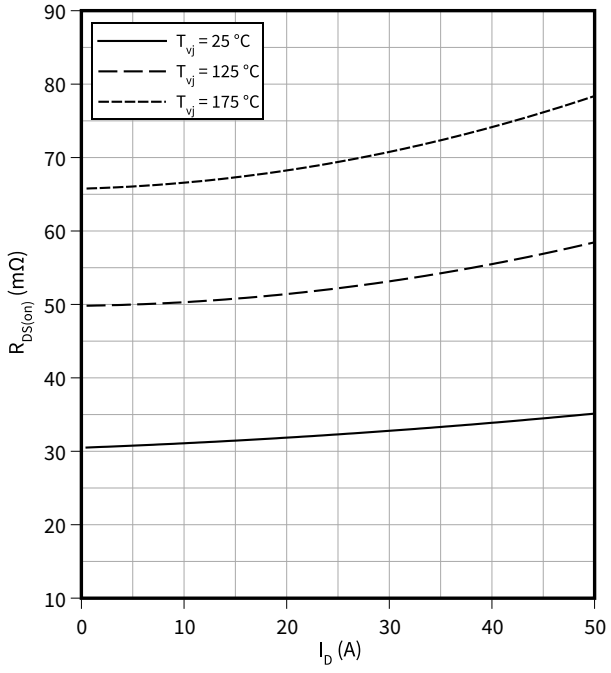
Output characteristic field (typical), MOSFET, T2 / T3

$I_D = f(V_{DS})$
$T_{vj} = 175\ °C$



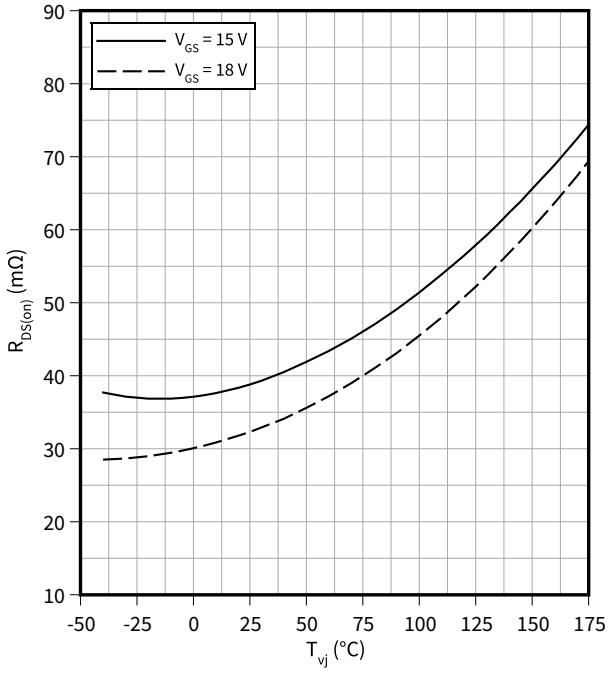
Drain source on-resistance (typical), MOSFET, T2 / T3

$R_{DS(on)} = f(I_D)$
$V_{GS} = 18\ V$



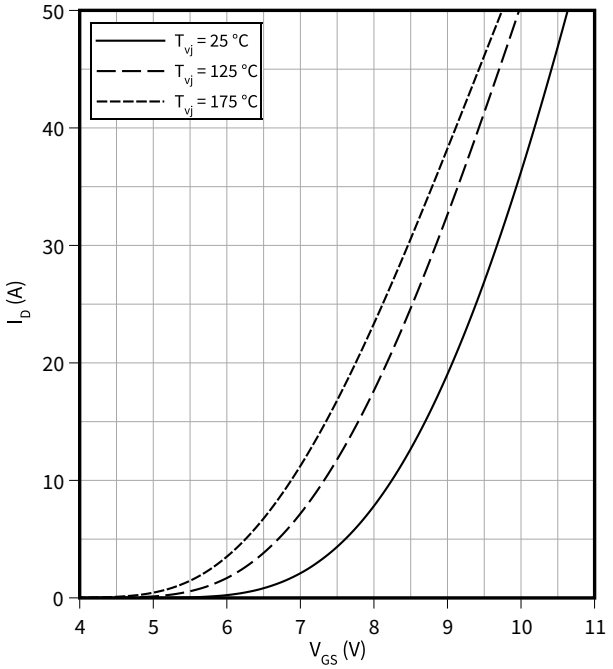
Drain source on-resistance (typical), MOSFET, T2 / T3

$R_{DS(on)} = f(T_{vj})$
$I_D = 25\ A$



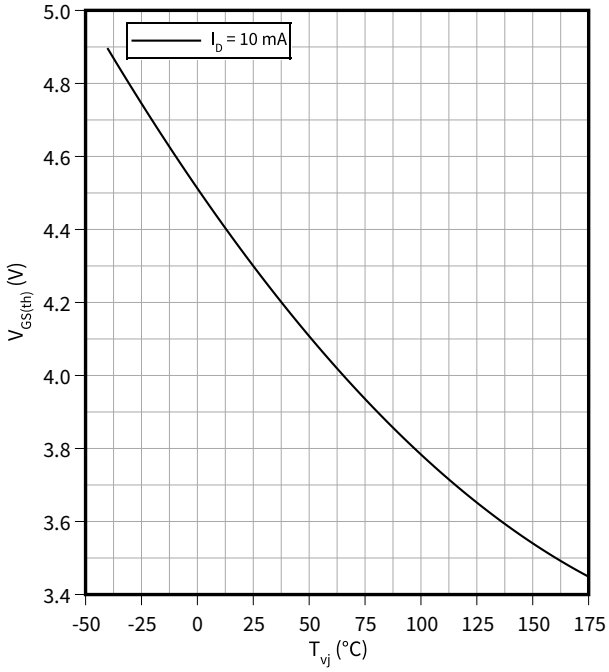
Transfer characteristic (typical), MOSFET, T2 / T3

$I_D = f(V_{GS})$
$V_{DS} = 20$ V



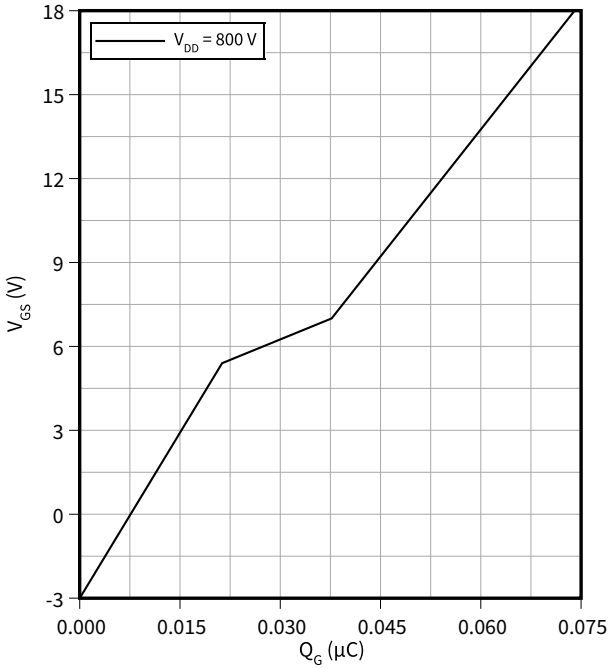
Gate-source threshold voltage (typical), MOSFET, T2 / T3

$V_{GS(th)} = f(T_{vj})$
$V_{GS} = V_{DS}$



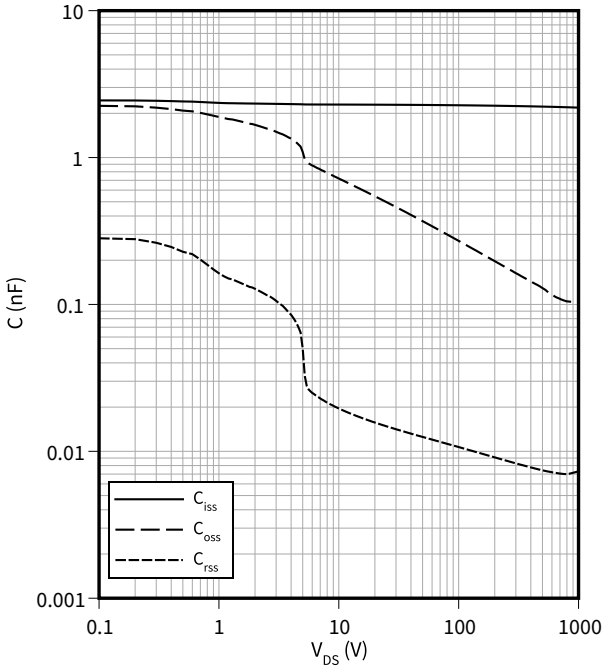
Gate charge characteristic (typical), MOSFET, T2 / T3

$V_{GS} = f(Q_G)$
$I_D = 25$ A, $T_{vj} = 25$ °C



Capacity characteristic (typical), MOSFET, T2 / T3

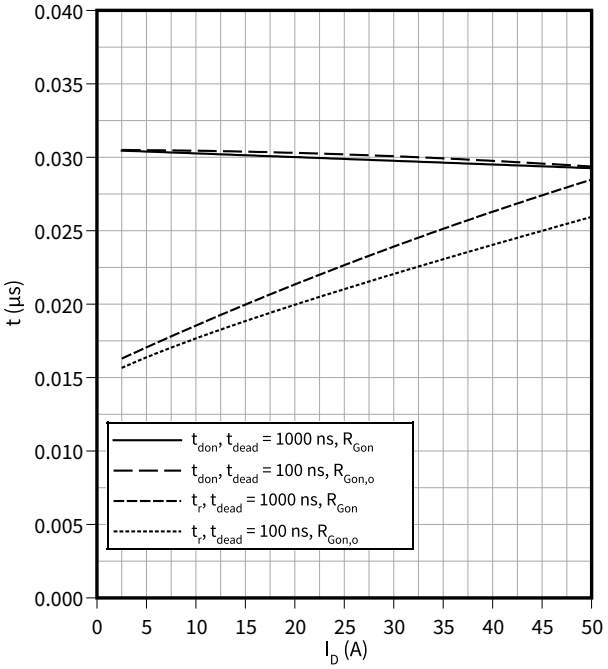
$C = f(V_{DS})$
$f = 100$ kHz, $T_{vj} = 25$ °C, $V_{GS} = 0$ V



Switching times (typical), MOSFET, T2 / T3

$t = f(I_D)$

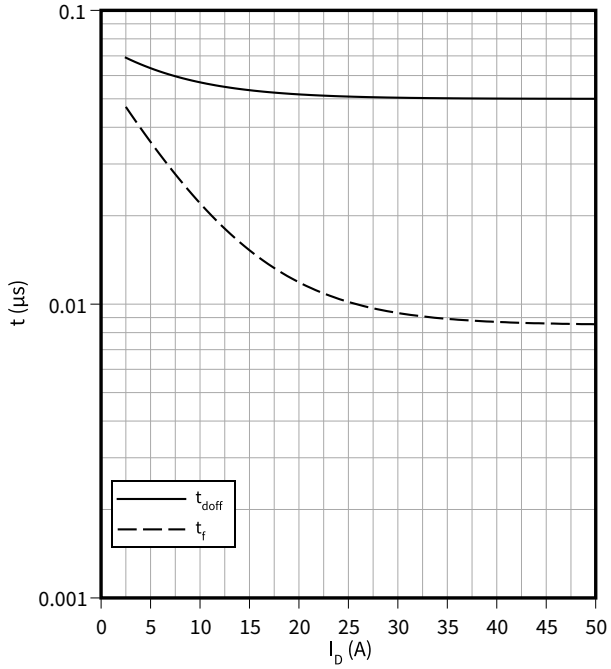
V_{DD} = 600 V, R_{Gon} = 4.7 Ω, $R_{Gon,o}$ = 4.3 Ω, T_{vj} = 175 °C, V_{GS} = -3/18 V



Switching times (typical), MOSFET, T2 / T3

$t = f(I_D)$

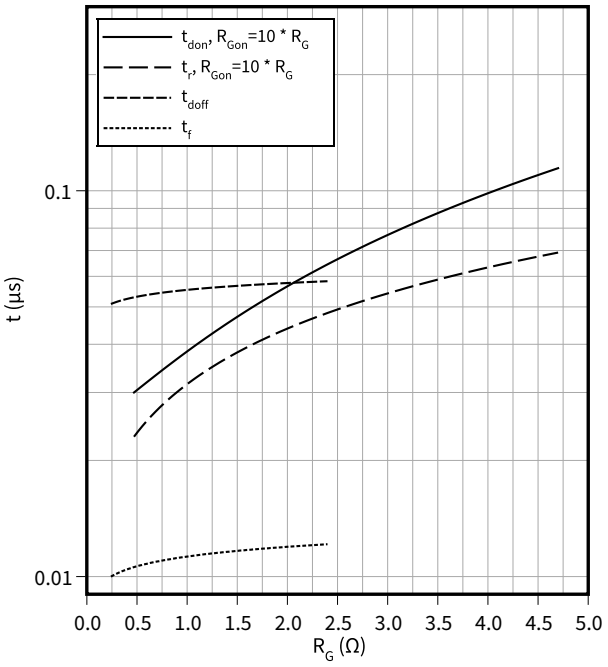
R_{Goff} = 0.24 Ω, V_{DD} = 600 V, T_{vj} = 175 °C, V_{GS} = -3/18 V



Switching times (typical), MOSFET, T2 / T3

$t = f(R_G)$

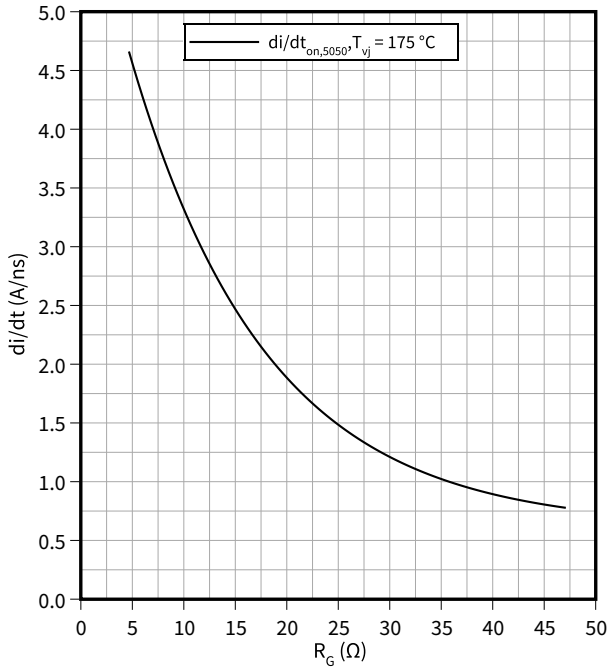
V_{DD} = 600 V, t_{dead} = 1000 ns, I_D = 25 A, T_{vj} = 175 °C, V_{GS} = -3/18 V



Current slope (typical), MOSFET, T2 / T3

$di/dt = f(R_G)$

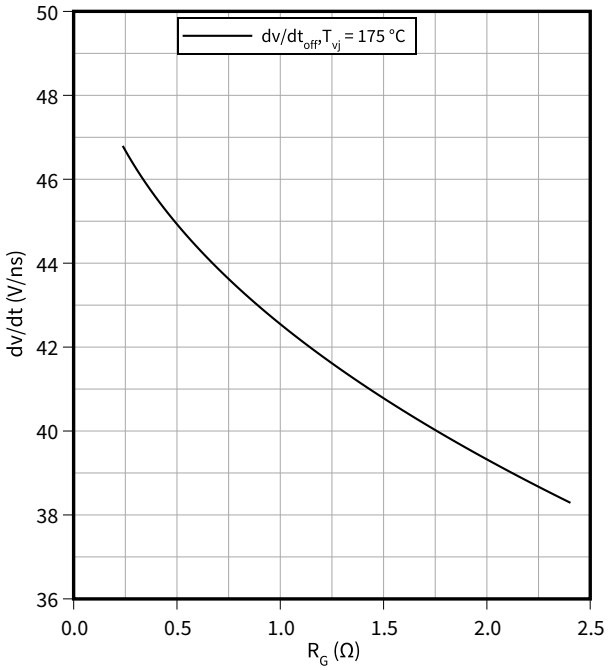
V_{DD} = 600 V, t_{dead} = 1000 ns, I_D = 25 A, V_{GS} = -3/18 V



Voltage slope (typical), MOSFET, T2 / T3

$dv/dt = f(R_G)$

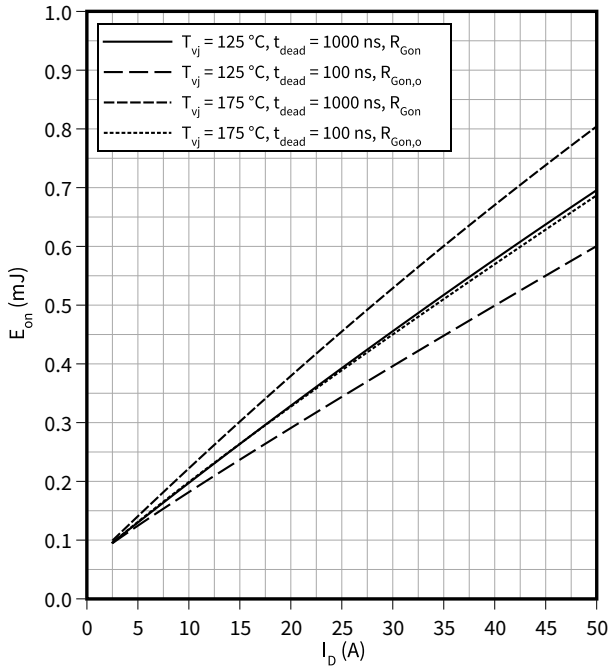
V_{DD} = 600 V, I_D = 25 A, V_{GS} = -3/18 V



Switching losses (typical), MOSFET, T2 / T3

$E_{on} = f(I_D)$

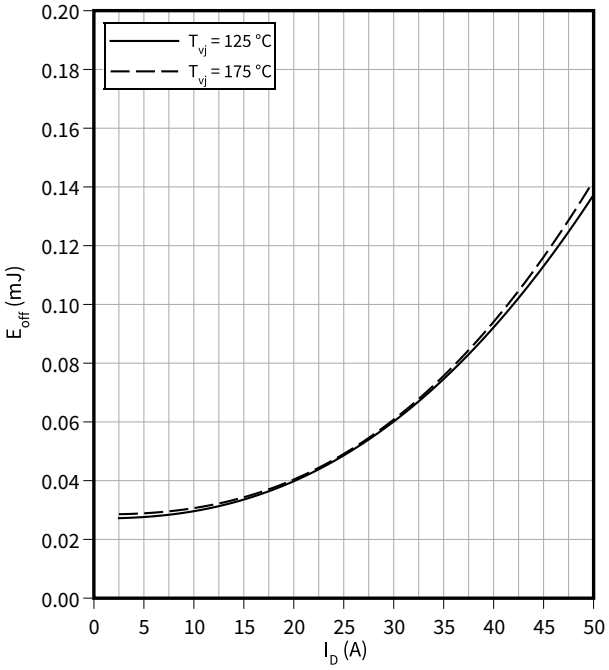
V_{DD} = 600 V, R_{Gon} = 4.7 Ω, $R_{Gon,o}$ = 4.3 Ω, V_{GS} = -3/18 V



Switching losses (typical), MOSFET, T2 / T3

$E_{off} = f(I_D)$

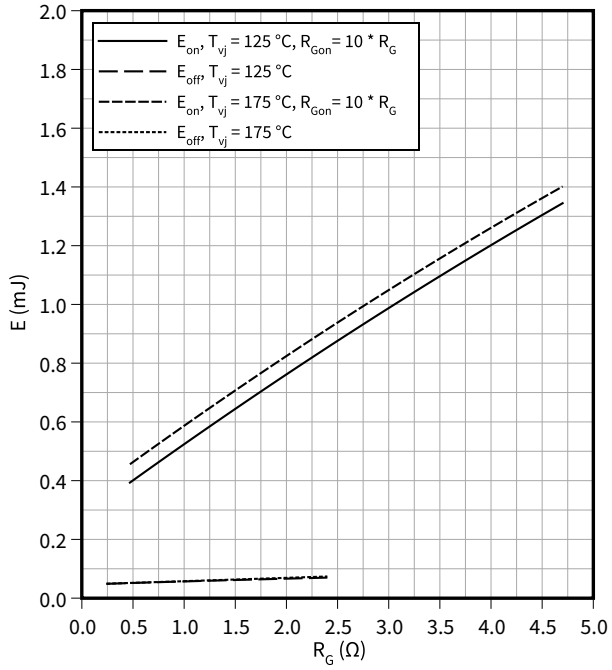
R_{Goff} = 0.24 Ω, V_{DD} = 600 V, V_{GS} = -3/18 V



Switching losses (typical), MOSFET, T2 / T3

$E = f(R_G)$

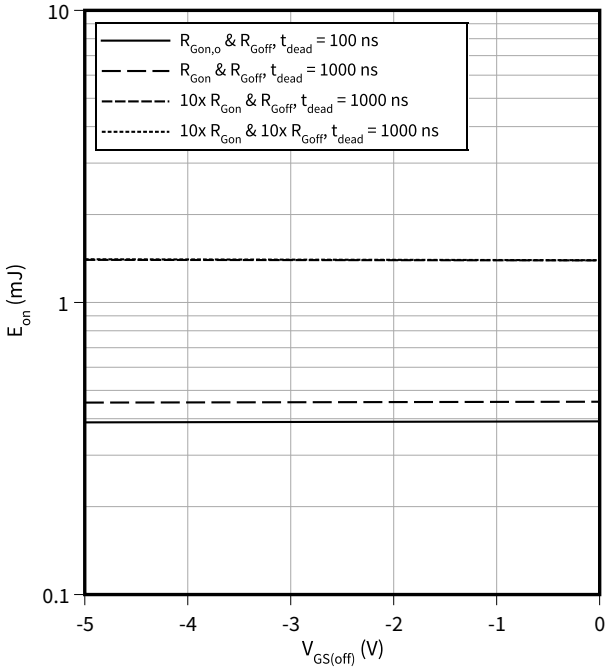
V_{DD} = 600 V, t_{dead} = 1000 ns, I_D = 25 A, V_{GS} = -3/18 V



Switching losses (typical), MOSFET, T2 / T3

$E_{on} = f(V_{GS(off)})$

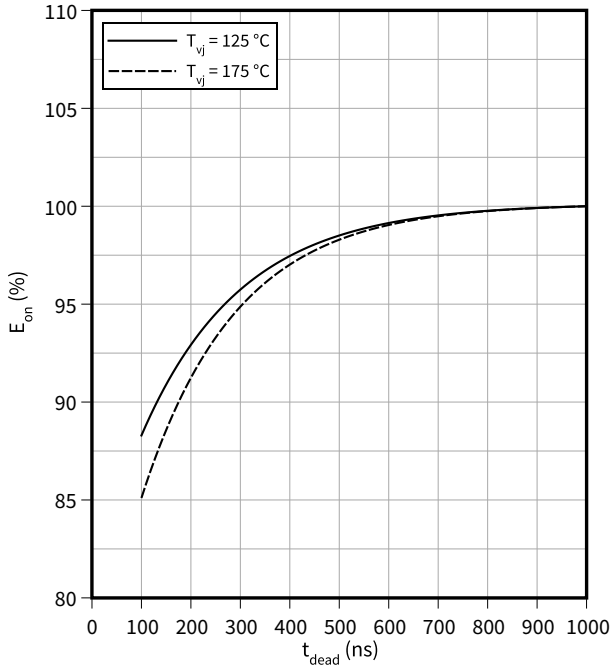
$R_{Goff} = 0.24\ \Omega$, $V_{DD} = 600$ V, $R_{Gon} = 4.7\ \Omega$, $V_{GS(on)} = 18$ V, $I_D = 25$ A, $R_{Gon,o} = 4.3\ \Omega$, $T_{vj} = 175$ °C



Switching losses (typical), MOSFET, T2 / T3

$E_{on} = f(t_{dead})$

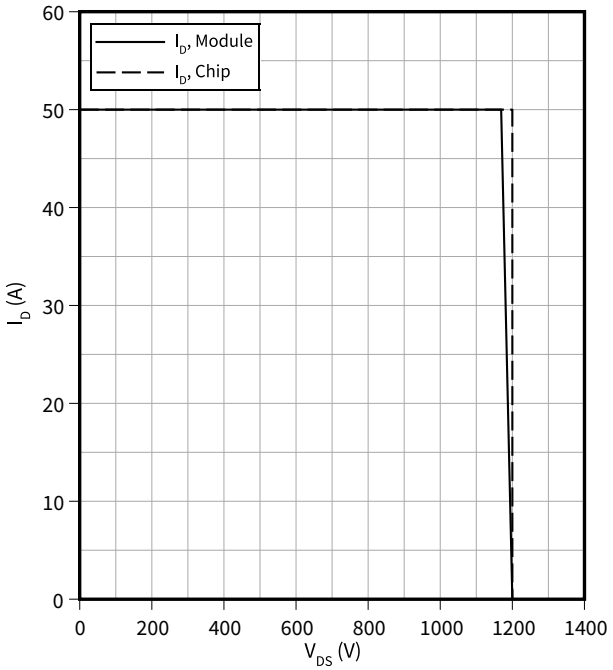
$R_{Gon} = 4.7\ \Omega$, $I_D = 25$ A, $V_{DD} = 600$ V, $V_{GS} = -3/18$ V



Reverse bias safe operating area (RBSOA), MOSFET, T2 / T3

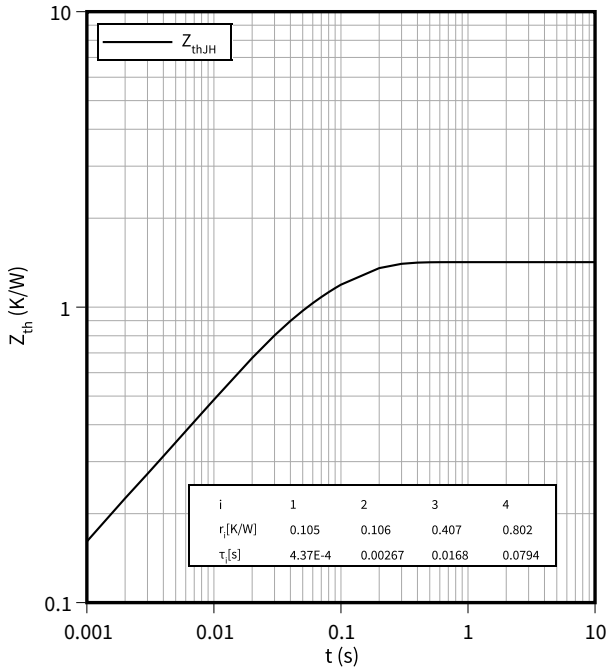
$I_D = f(V_{DS})$

$R_{Goff} = 0.24\ \Omega$, $T_{vj} = 175$ °C, $V_{GS} = -3/18$ V



Transient thermal impedance, MOSFET, T2 / T3

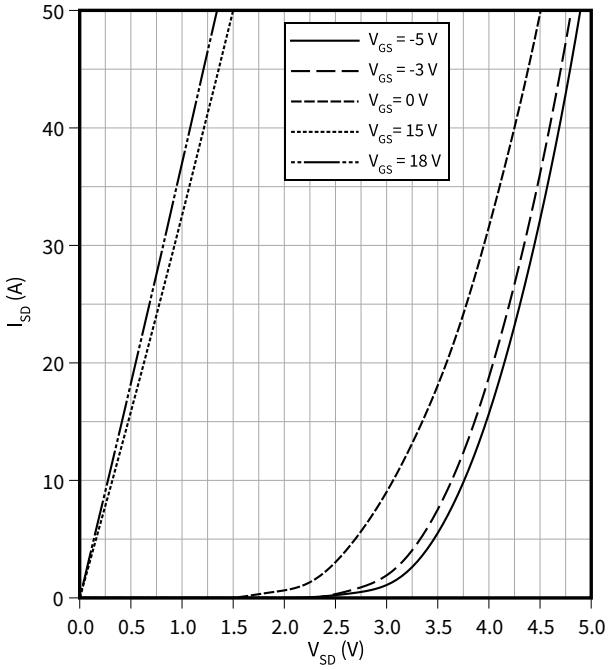
$Z_{th} = f(t)$



Forward characteristic body diode (typical), MOSFET, T2 / T3

$I_{SD} = f(V_{SD})$

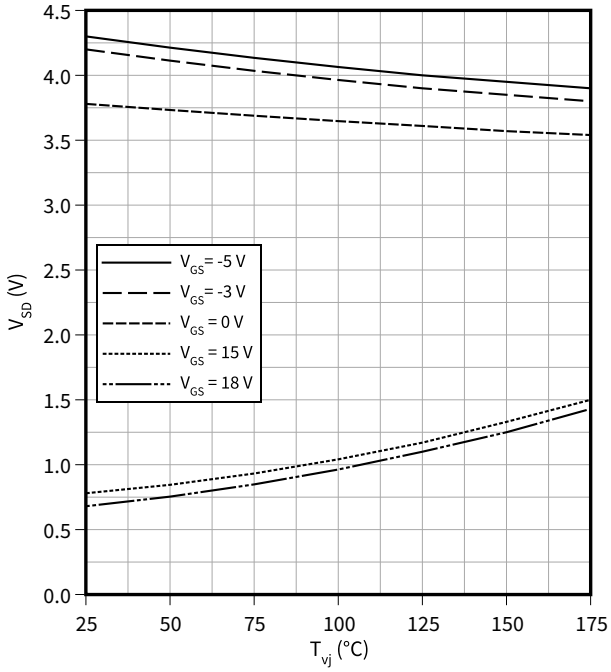
$T_{vj} = 25\ °C$



Forward characteristic body diode (typical), MOSFET, T2 / T3

$V_{SD} = f(T_{vj})$

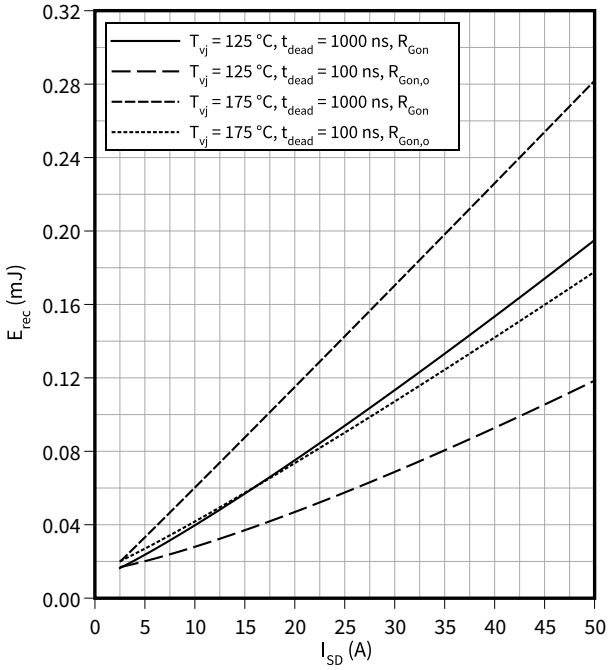
$I_{SD} = 25\ A$



Switching losses body diode (typical), MOSFET, T2 / T3

$E_{rec} = f(I_{SD})$

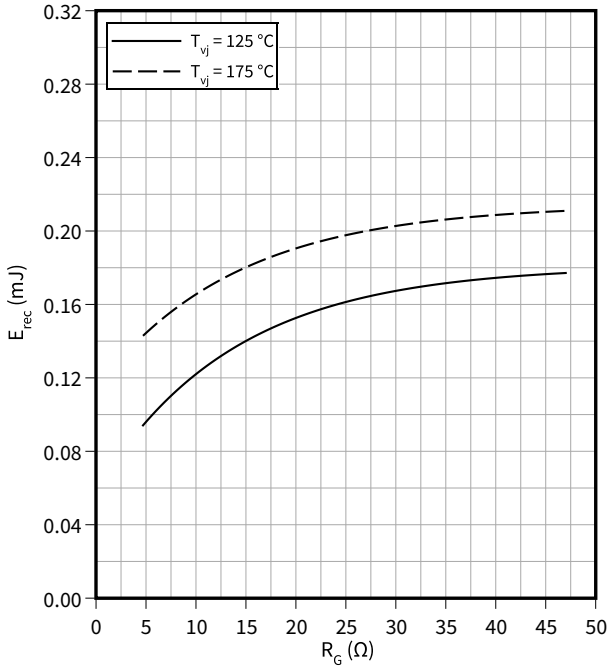
$R_{Gon} = 4.7\ \Omega$, $R_{Gon,o} = 4.3\ \Omega$, $V_{DD} = 600\ V$



Switching losses body diode (typical), MOSFET, T2 / T3

$E_{rec} = f(R_G)$

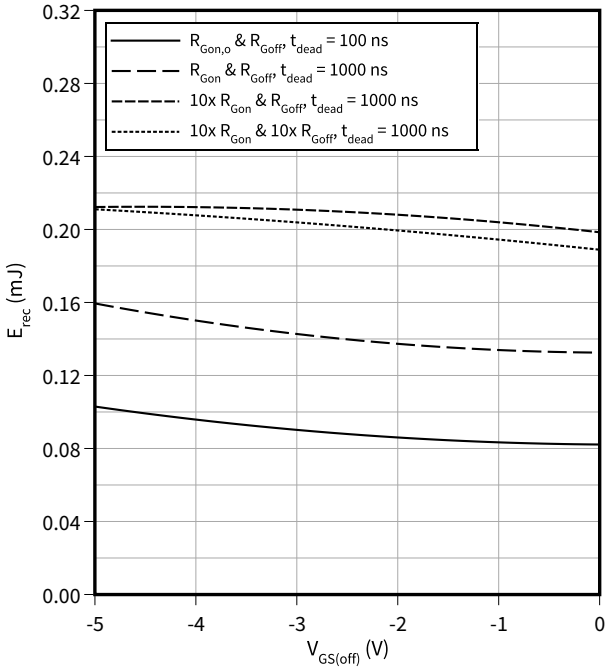
$t_{dead} = 1000\ ns$, $I_{SD} = 25\ A$, $V_{DD} = 600\ V$



Switching losses body diode (typical), MOSFET, T2 / T3

$E_{rec} = f(V_{GS(off)})$

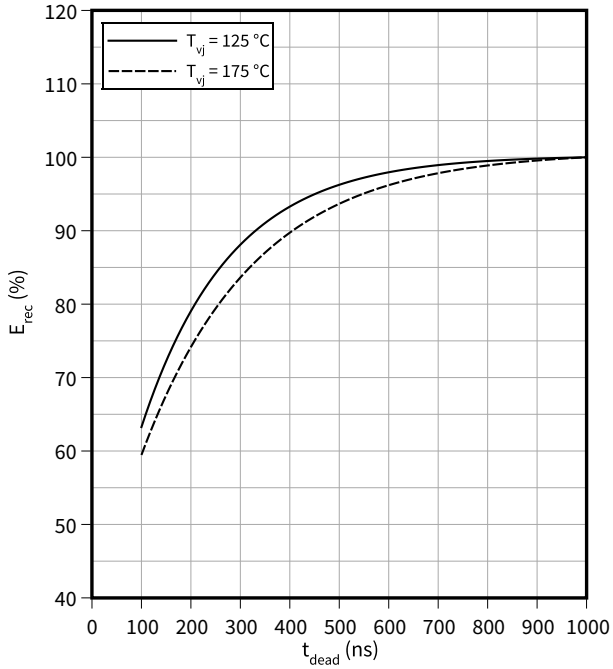
R_{Goff} = 0.24 Ω, R_{Gon} = 4.7 Ω, $V_{GS(on)}$ = 18 V, I_{SD} = 25 A, $R_{Gon,o}$ = 4.3 Ω, V_{DD} = 600 V, T_{vj} = 175 °C



Switching losses body diode (typical), MOSFET, T2 / T3

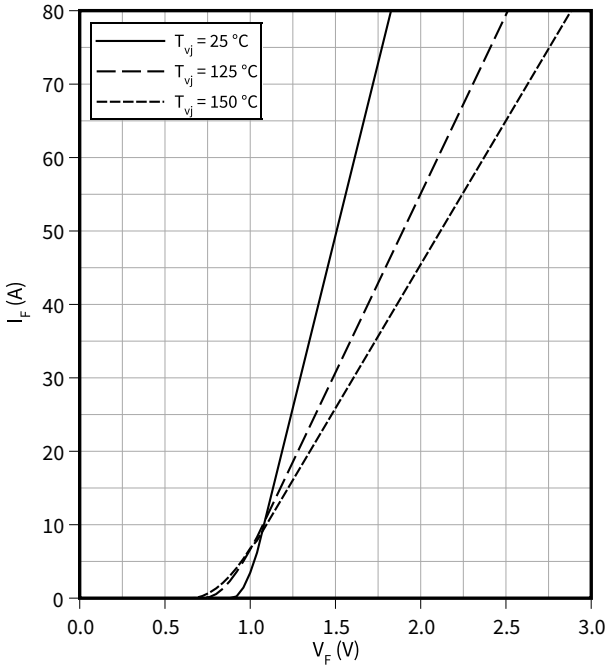
$E_{rec} = f(t_{dead})$

R_{Gon} = 4.7 Ω, I_D = 25 A, V_{DD} = 600 V, V_{GS} = -3/18 V



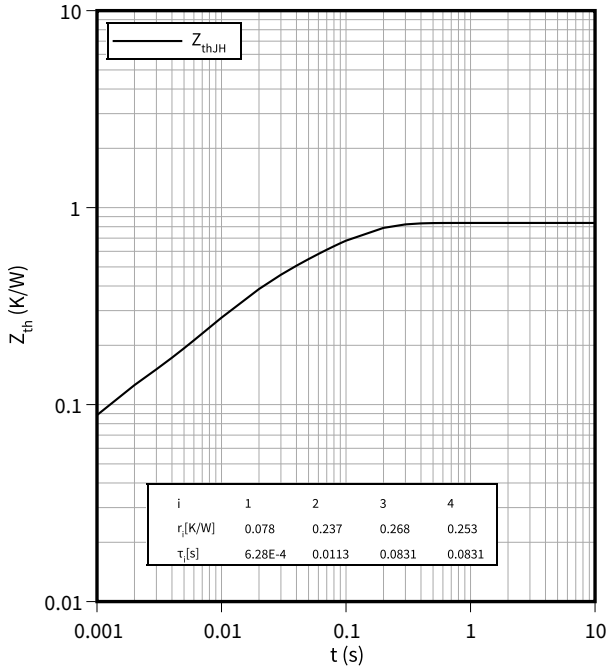
Forward characteristic (typical), Diode, Boost

$I_F = f(V_F)$



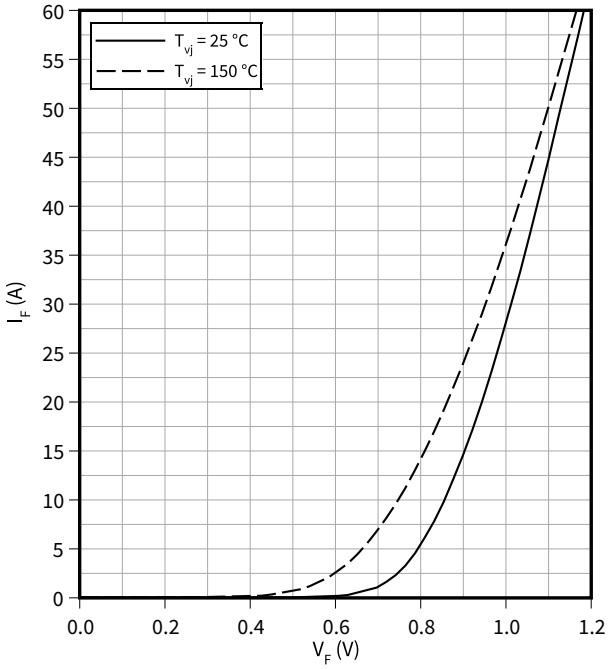
Transient thermal impedance, Diode, Boost

$Z_{th} = f(t)$



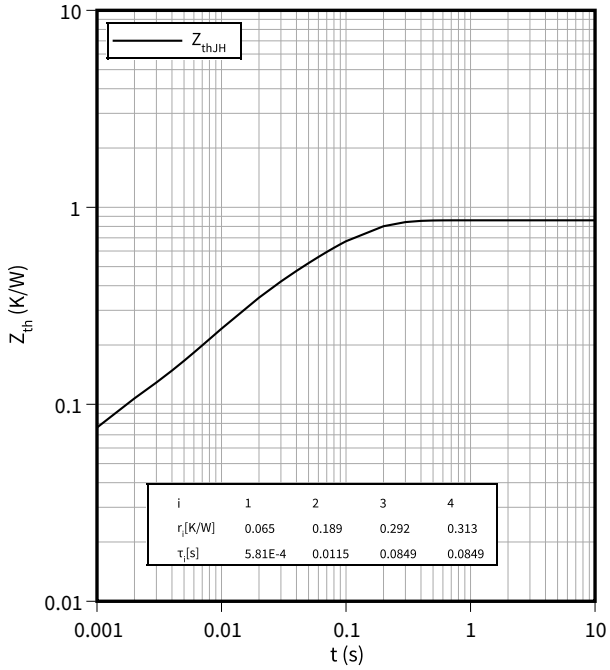
Forward characteristic (typical), Bypass-diode

$I_F = f(V_F)$



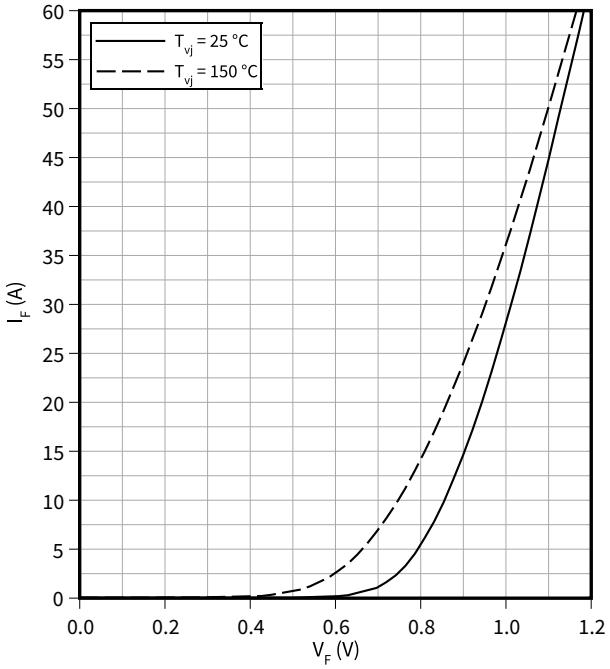
Transient thermal impedance, Bypass-diode

$Z_{th} = f(t)$



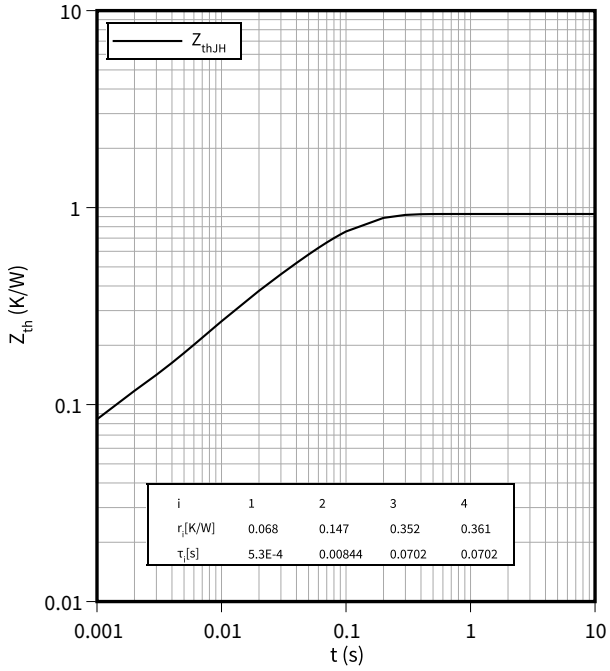
Forward characteristic (typical), Inverse-polarity protection diode

$I_F = f(V_F)$



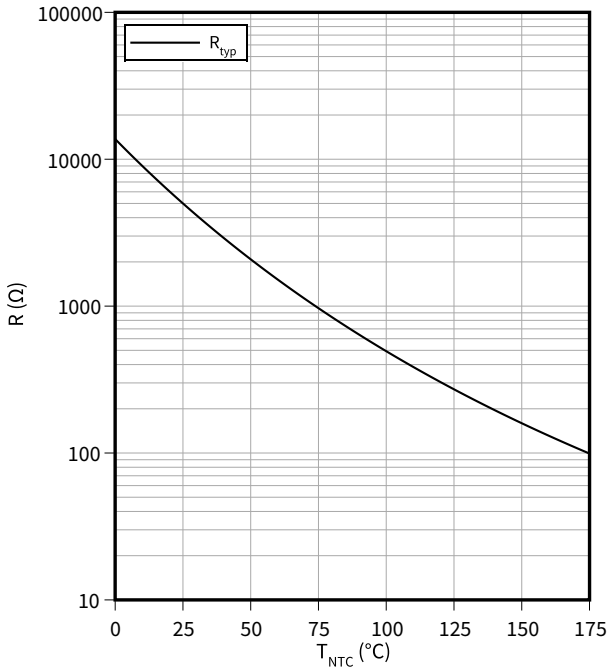
Transient thermal impedance, Inverse-polarity protection diode

$Z_{th} = f(t)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



11 Circuit diagram

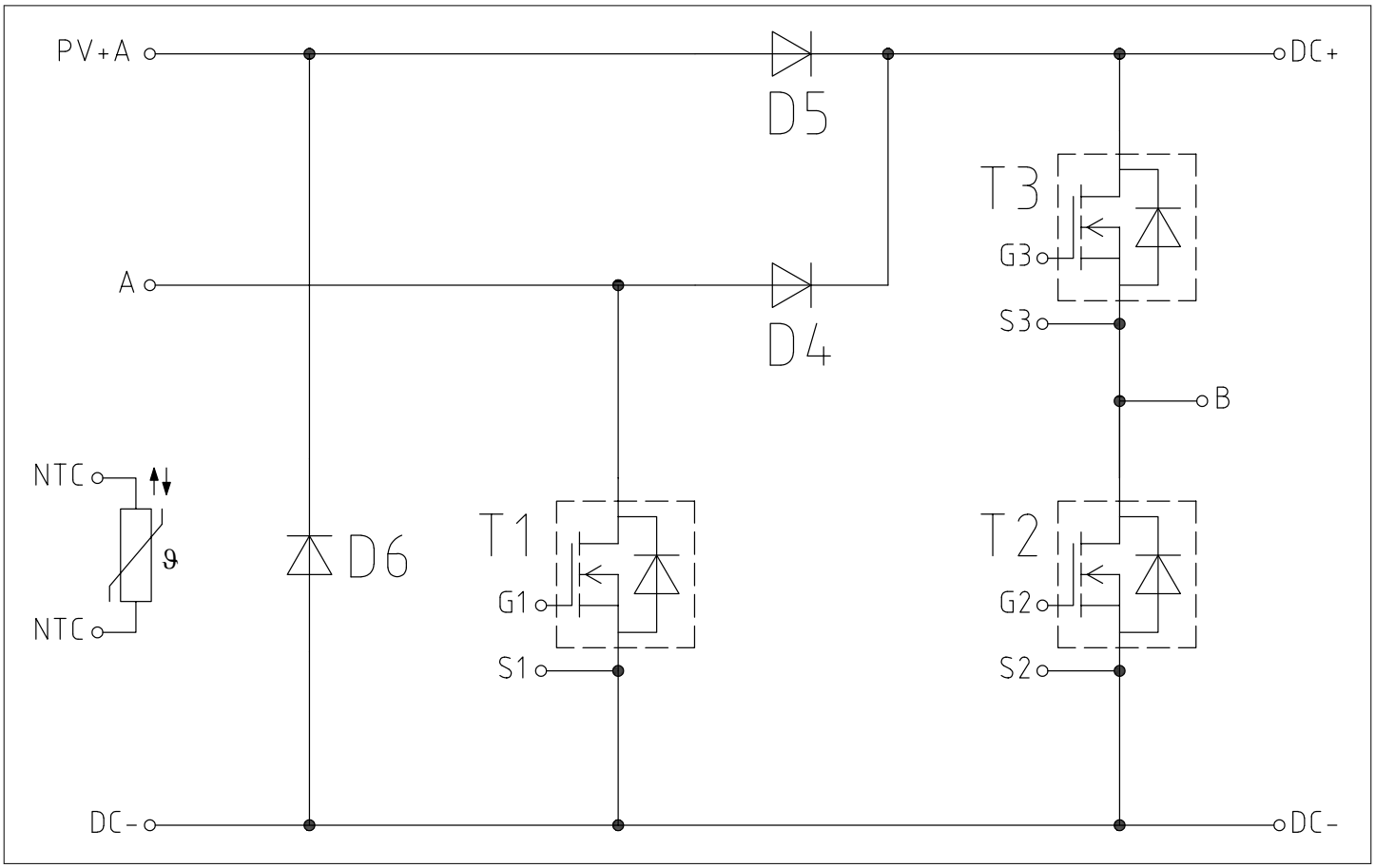


Figure 1

12 Package outlines

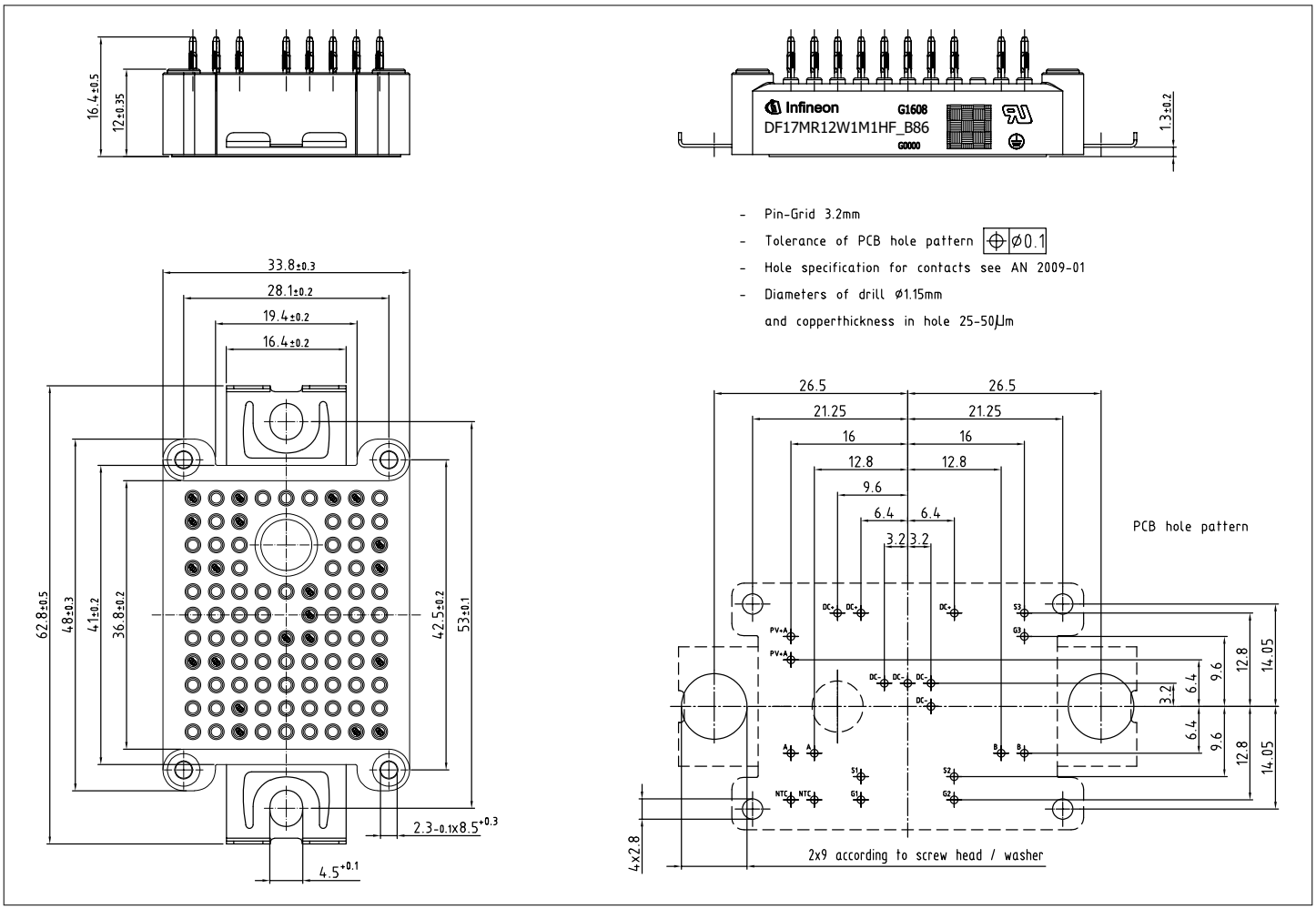


Figure 2

13 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	*Content* Module serial number Module material number Production order number Date code (production year) Date code (production week)	*Digit* 1 – 5 6 - 11 12 - 19 20 – 21 22 – 23	*Example* 71549 142846 55054991 15 30
Example	7154914284655054991530		7154914284655054991530

Figure 3

Revision history

Document version	Date of release	Description of changes
0.10	2024-07-03	Initial version
0.20	2024-10-01	Target datasheet
1.00	2024-12-12	Final datasheet

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